SQM120N06-3m5L_RC



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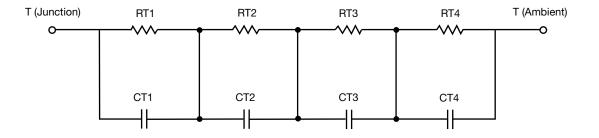
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	21.8851	112.4357m	N/A			
RT2	3.3856	93.9415m	N/A			
RT3	777.2462m	118.4911m	N/A			
RT4	13.9006	75.8615m	N/A			
	THERMAL CAPACI	TANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	4.6123	168.2609m	N/A			
CT2	1.0693	53.5222m	N/A			
CT3	53.1968m	8.7304m	N/A			
CT4	6.6023	889.3930m	N/A			

Note

• n/a indicates not applicable

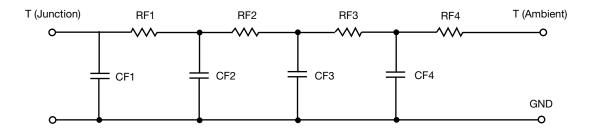
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.





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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	1.3207	143.7166m	N/A		
RF2	5.4727	140.3574m	N/A		
RF3	26.7163	111.3036m	N/A		
RF4	6.3731	4.5934m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	56.3746m	6.9911m	N/A		
CF2	945.5625m	28.3065m	N/A		
CF3	1.7131	295.4169m	N/A		
CF4	234.6497m	66.5661m	N/A		

Note

• n/a indicates not applicable

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